

General Description

The AGM603C combines advanced trenchMOSFET technology with a low resistance package to provide extremely low $R_{DS(ON)}$.

This device is ideal for load switch and battery protection applications.

Features

- Advance high cell density Trench technology
- Low $R_{DS(ON)}$ to minimize conductive loss
- Low Gate Charge for fast switching
- Low Thermal resistance
- 100% Avalanche tested
- 100% DVDS tested

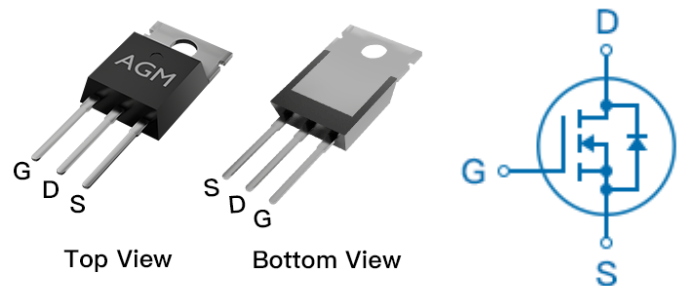
Application

- MB/VGA Vcore
- SMPS 2nd Synchronous Rectifier
- POL application
- BLDC Motor driver

Product Summary

BVDSS	RDSON	ID
60V	3.0mΩ	130A

TO-220 Pin Configuration



Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
AGM603C	AGM603C	TO-220	----	----	1000

Table 1. Absolute Maximum Ratings (TC=25°C)

Symbol	Parameter	Value	Unit
VDS	Drain-Source Voltage (VGS=0V)	60	V
VGS	Gate-Source Voltage (VDS=0V)	±20	V
ID	Drain Current-Continuous(Tc=25°C) (Note 1)	130	A
	Drain Current-Continuous(Tc=100°C)	78	A
IDM (pluse)	Drain Current-Pulsed (Note 2)	520	A
PD	Maximum Power Dissipation(Tc=25°C)	140	w
	Maximum Power Dissipation(Tc=100°C)	56	w
EAS	Avalanche energy (Note 3)	441	mJ
TJ,TSTG	Operating Junction and Storage Temperature Range	-55 To 150	°C

Table 2. Thermal Characteristic

Symbol	Parameter	Typ	Max	Unit
RθJA	Thermal Resistance Junction-ambient (Steady State) ¹	---	62	°C/W
RθJC	Thermal Resistance Junction-Case ¹	---	0.89	°C/W

Table 3. Electrical Characteristics (Tj=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
On/Off States						
BVDSS	Drain-Source Breakdown Voltage	VGS=0V ID=250μA	60	--	--	V
IDSS	Zero Gate Voltage Drain Current	VDS=60V,VGS=0V	--	--	1	μA
IGSS	Gate-Body Leakage Current	VGS=±20V,VDS=0V	--	--	±100	nA
VGS(th)	Gate Threshold Voltage	VDS=VGS,ID=250μA	1.2	1.6	2.2	V
gFS	Forward Transconductance	VDS=5V,ID=10A	--	5	--	S
RDS(on)	Drain-Source On-State Resistance	VGS=10V, ID=20A	--	3.0	3.8	mΩ
		VGS=4.5V, ID=10A	--	3.5	5.7	mΩ
Dynamic Characteristics						
Ciss	Input Capacitance	VDS=25V,VGS=0V, F=1MHZ	--	3716	--	pF
Coss	Output Capacitance		--	883	--	pF
Crss	Reverse Transfer Capacitance		--	35	--	pF
Rg	Gate resistance	VGS=0V, VDS=0V,f=1.0MHz	--	1.5	--	Ω
Switching Times						
td(on)	Turn-on Delay Time	VGS=10V,VDS=30V, ID=25A,RGEN=2Ω	--	22.5	--	nS
tr	Turn-on Rise Time		--	6.7	--	nS
td(off)	Turn-Off Delay Time		--	80.3	--	nS
tf	Turn-Off Fall Time		--	26.8	--	nS
Qg	Total Gate Charge	VGS=10V, VDS=30V, ID=25A	--	66.1	--	nC
Qgs	Gate-Source Charge		--	10.7	--	nC
Qgd	Gate-Drain Charge		--	10.9	--	nC
Source-Drain Diode Characteristics						
ISD	Source-Drain Current(Body Diode)		--	--	130	A
VSD	Forward on Voltage	VGS=0V,IS=20A	--	--	1.2	V
trr	Reverse Recovery Time	IF=20A , dI/dt=100A/μs , TJ=25℃	--	68.3	--	ns
Qrr	Reverse Recovery Charge		--	73	--	nc

Notes 1.The maximum current rating is package limited.

Notes 2.Repetitive Rating: Pulse width limited by maximum junction temperature

Notes 3.EAS condition: TJ=25°C,VDD=30V,Vgs=10V,ID=42A, L=0.5mH,RG=25ohm

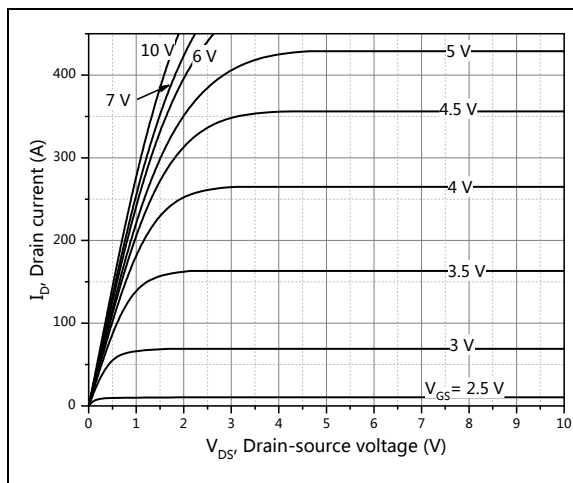


Figure 1, Typ. output characteristics

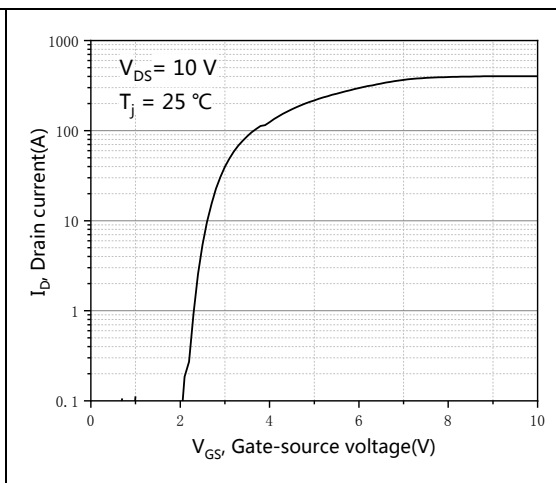


Figure 2, Typ. transfer characteristics

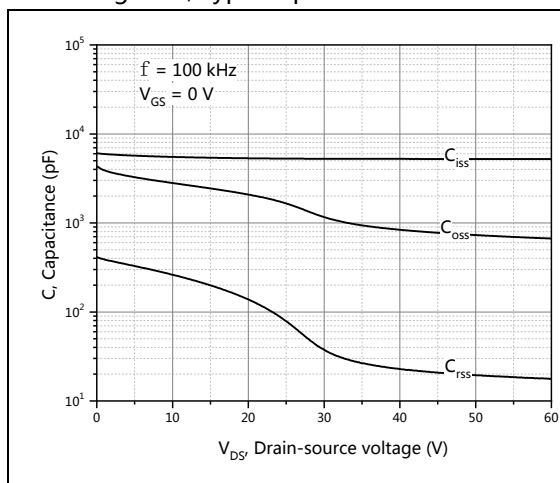


Figure 3, Typ. capacitances

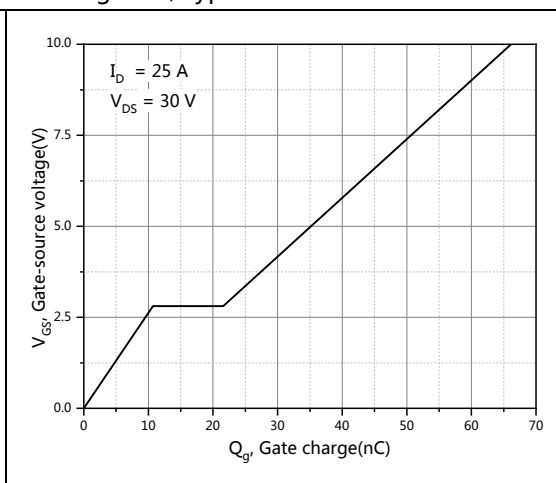


Figure 4, Typ. gate charge

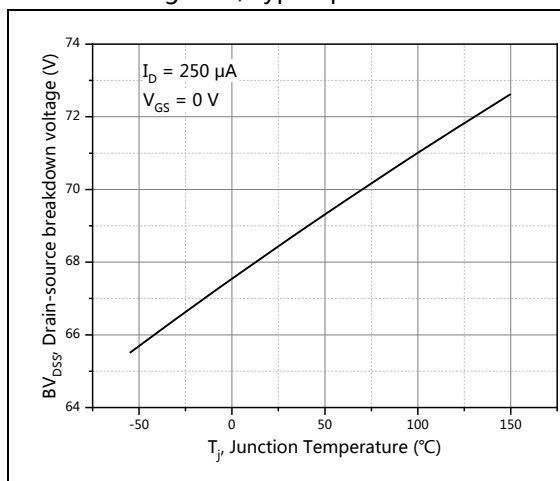


Figure 5, Drain-source breakdown voltage

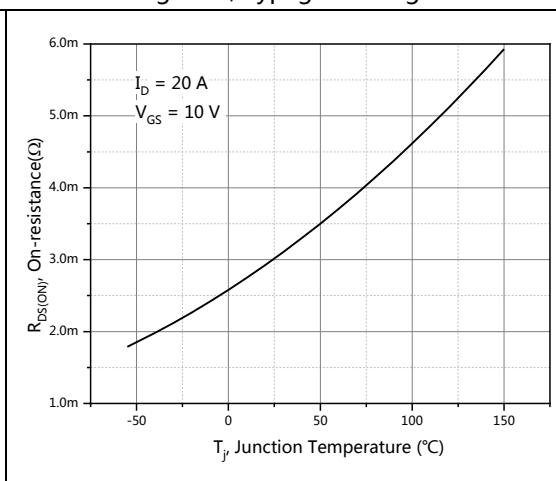


Figure 6, Drain-source on-state resistance

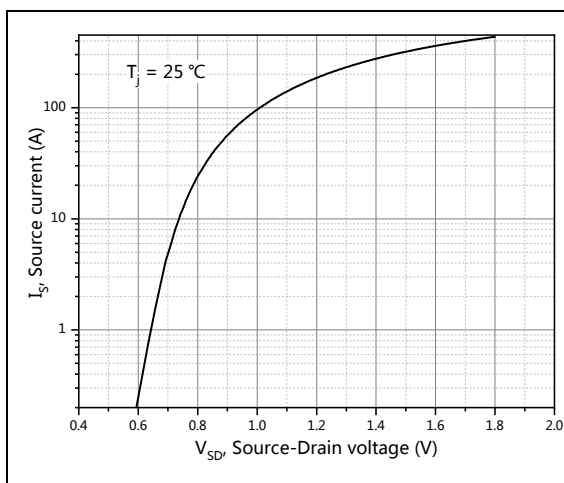


Figure 7, Forward characteristic of body diode

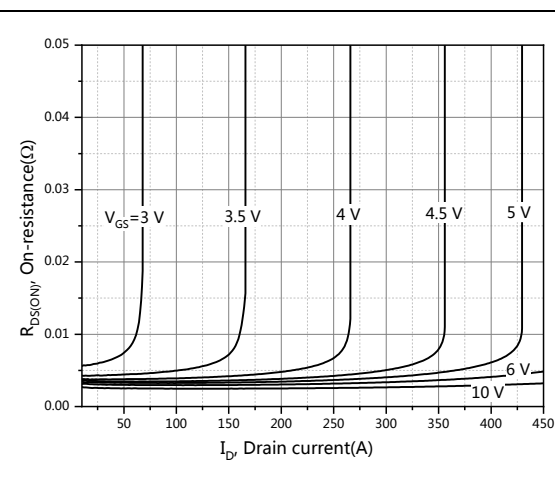


Figure 8, Drain-source on-state resistance

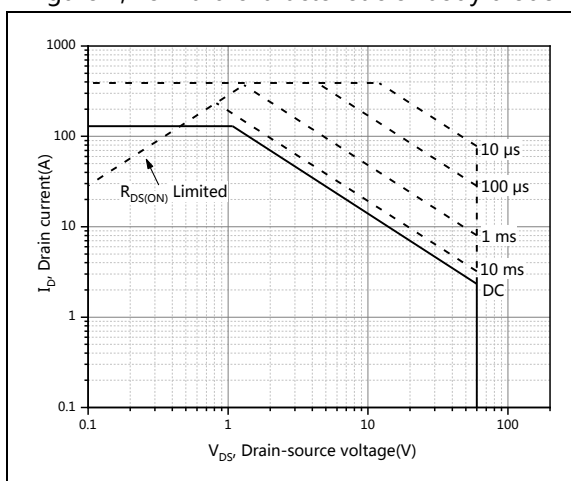


Figure 9, Safe operation area $T_C=25\text{ }^{\circ}\text{C}$

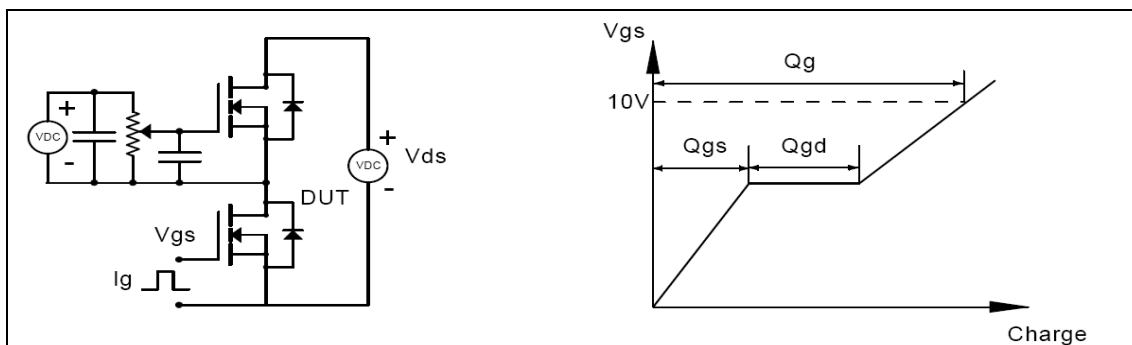


Figure 1, Gate charge test circuit & waveform

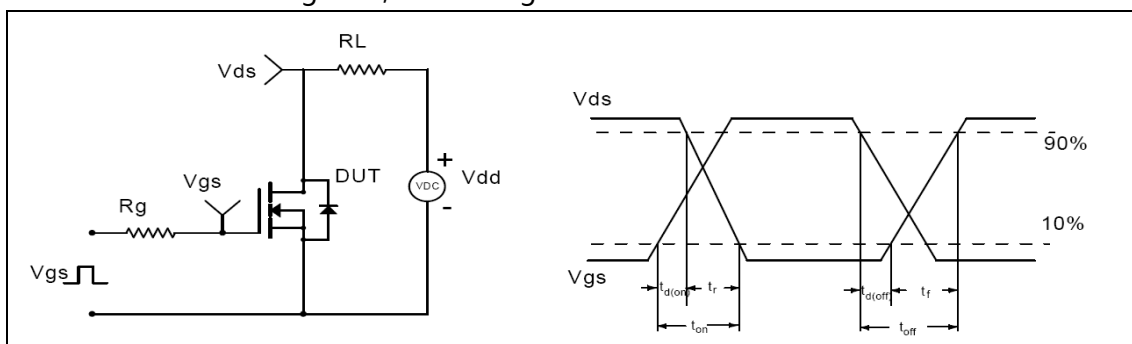


Figure 2, Switching time test circuit & waveforms

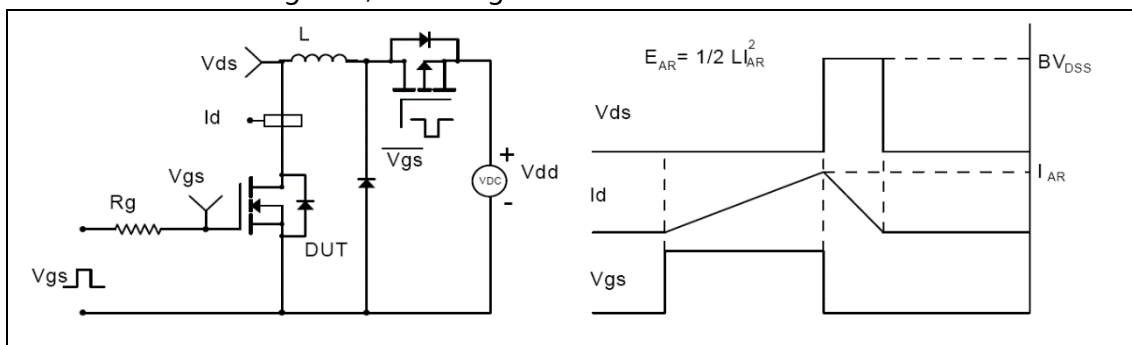


Figure 3, Unclamped inductive switching (UIS) test circuit & waveforms

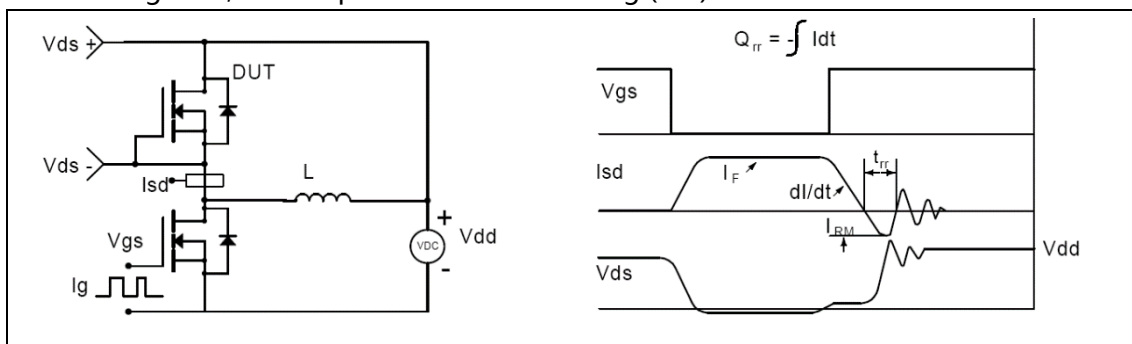
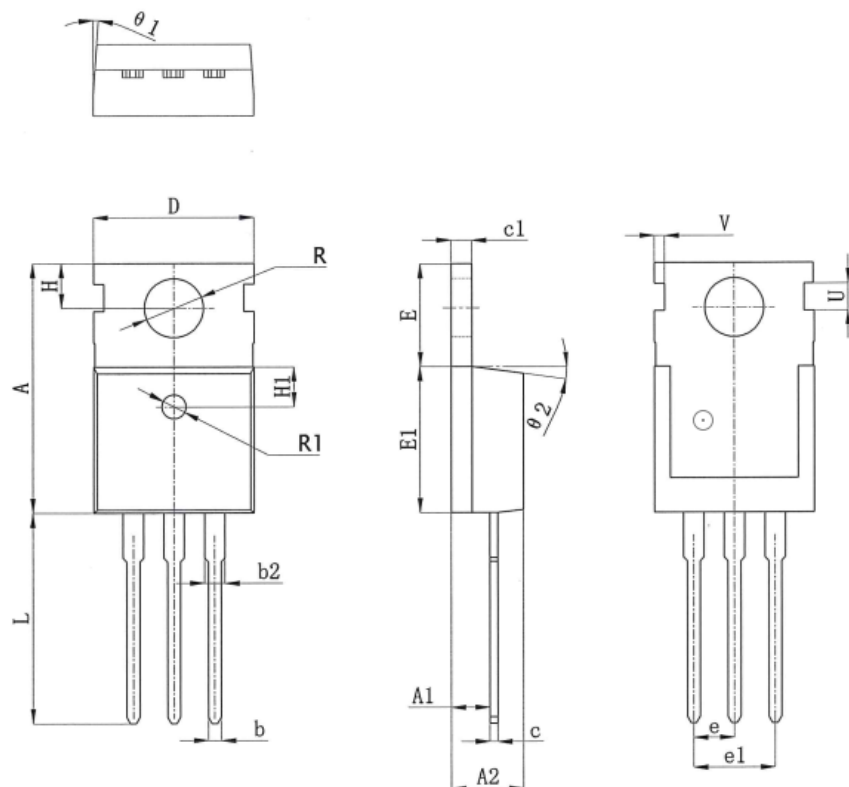
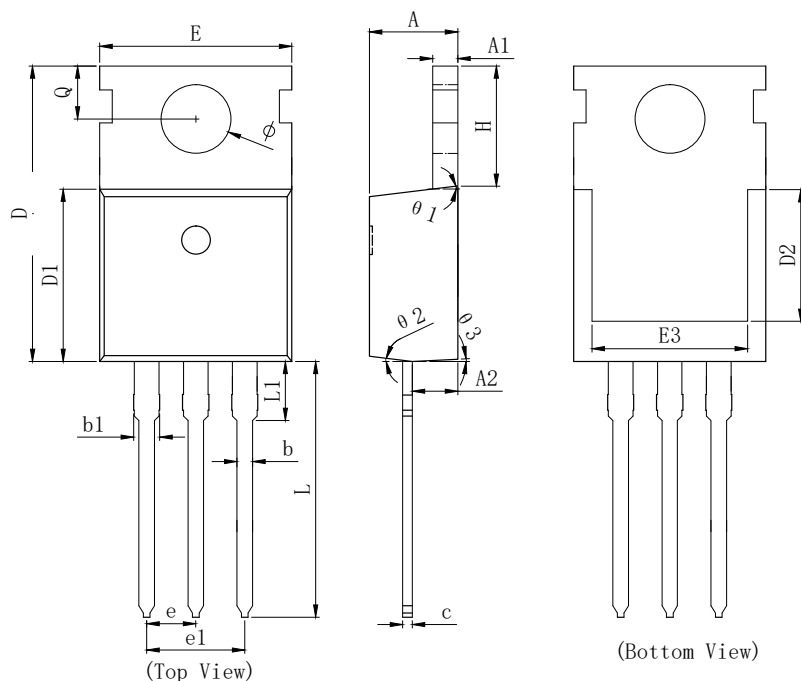


Figure 4, Diode reverse recovery test circuit & waveforms

TO-220 PACKAGE INFORMATION



SYMBOL	MILLIMETER		
	MIN	NOM	MAX
A	15.400	15.600	15.800
A1	2.350	2.400	2.500
A2	4.400	4.500	4.700
b	0.700	0.800	0.900
b2	1.180	1.310	1.440
c	0.480	0.500	0.560
c1	1.290	1.300	1.320
D	9.800	10.000	10.200
E	6.400	6.500	6.600
E1	9.000	9.100	9.200
e	2.420	2.540	2.660
e1	4.840	5.080	5.320
H	2.730	2.800	2.870
H1	2.400	2.500	2.600
L	13.020	13.370	13.720
R	3.500	3.600	3.730
R1	1.400	1.500	1.600
U	1.650	1.750	1.850
V	0.580	0.680	0.780
θ_1	2°	2.5°	3°
θ_2	6.5°	7°	7.5°



SYMBOL	MILLIMETER		
	MIN	Typ.	MAX
A	4.370	4.570	4.700
A1	1.250	1.300	1.400
A2	2.150	2.350	2.550
b	0.700	0.800	0.950
b1	1.170	1.270	1.470
c	0.450	0.500	0.600
D	15.100	15.600	16.100
D1	8.800	9.100	9.400
D2	5.500	6.300 REF	
E	9.700	10.000	10.300
E3	7.000	7.600 REF	
e	2.540 BSC		
e1	5.080 BSC		
L	13.200	13.500	13.800
L1		3.100	3.400
H	6.250	6.500	6.750
ϕ	3.400	3.600	3.800
Q	2.600	2.800	3.000
θ_1	7° TYP		
θ_2	7° TYP		
θ_3	3° TYP		

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